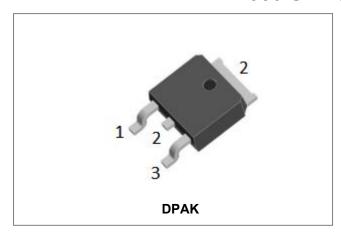






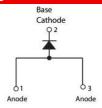
### **MBRD660 SCHOTTKY RECTIFIER**



#### **Features**

- 150℃ T<sub>J</sub> operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- "-A" is an AEC-Q101 qualified device
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

### **Circuit Diagram**



#### **Applications**

- Disk drives
- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Battery charging

#### **Maximum Ratings:**

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	-	60	V
Average Rectified Forward Current	I <sub>F (AV)</sub>	50% duty cycle @Tc=85°C, rectangular wave form	6	Α
Peak One Cycle Non-Repetitive Surge Current	I <sub>FSM</sub>	8.3ms, Half Sine pulse	125	Α

#### **Electrical Characteristics:**

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	V <sub>F1</sub>	@ 6A, Pulse, T <sub>J</sub> = 25 °C	0.70	0.75	V
	V <sub>F2</sub>	@ 6A, Pulse, T <sub>J</sub> = 125 °C	0.60	0.70	V
Reverse Current *	I <sub>R1</sub>	@V <sub>R</sub> = rated V <sub>R</sub> , T <sub>J</sub> = 25 °C	0.01	1	mA
	I <sub>R2</sub>	@V <sub>R</sub> = rated V <sub>R</sub> , T <sub>J</sub> = 125 °C	3	10	mA
Junction Capacitance	Ст	$@V_R = 5.0V, T_C = 25 °C$ $f_{SIG} = 1MHz$	300	400	pF

<sup>\*</sup> Pulse width < 300  $\mu$ s, duty cycle < 2%



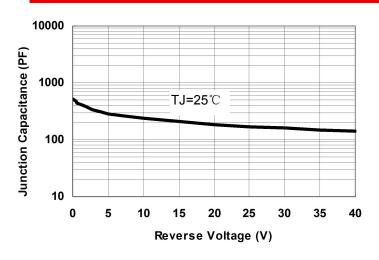




### **Thermal-Mechanical Specifications:**

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +150	°C
Storage Temperature	T <sub>stg</sub>	-	-55 to +150	°C
Typical Thermal Resistance Junction to Case	R <sub>θ</sub> JC	-	6	°C/W
Approximate Weight	wt	-	0.39	g
Case Style	DPAK			

### **Ratings and Characteristics Curves**



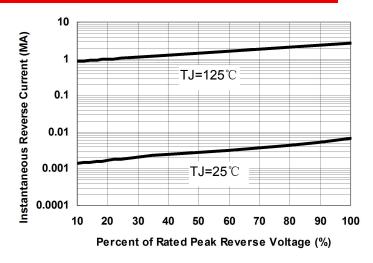


Fig.1-Typical Junction Capacitance

Fig.2-Typical Reverse Characteristics

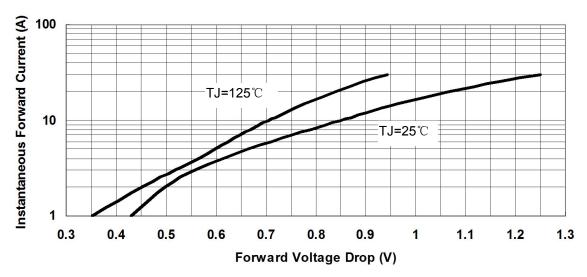


Fig.3-Typical Instantaneous Forward Voltage Characteristics

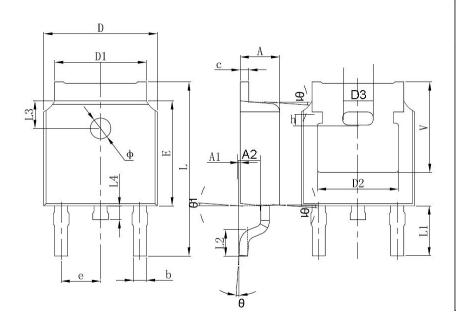
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### **Mechanical Dimensions DPAK**



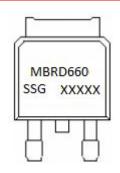
CVMDOL	Millimeters		Inches		
SYMBOL	Min.	Max.	Min.	Max.	
Α	2.20	2.40	0.087	0.094	
A1	0.00	0.127	0.000	0.005	
b	0.66	0.86	0.026	0.034	
С	0.46	0.60	0.018	0.024	
D	6.50	6.70	0.256	0.264	
D1	5.13	5.46	0.202	0.215	
D2	4.83 REF.		0.190 REF.		
Е	6.00	6.20	0.236	0.244	
е	2.186	2.386	0.086	0.094	
L	9.70	10.40	0.381	0.409	
L1	2.90 REF.		0.144 REF.		
L2	1.40	1.70	0.055	0.067	
L3	1.60 REF.		0.063 REF.		
L4	0.60	1.00	0.024	0.039	
Ф	1.10	1.30	0.043	0.051	
Θ	0°	8°	0°	8°	
h	0.00	0.30	0.000	0.012	
V	5.35 REF.		0.211 REF.		

### **Ordering Information**

Device	Package	Shipping
MBRD660	DPAK (Pb-Free)	2500pcs / reel
MBRD660TR	DPAK (Pb-Free)	2500pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

# **Marking Diagram**



Where XXXXX is YYWWL

 MBRD660
 = Part Name

 SSG
 = SSG

 YY
 = Year

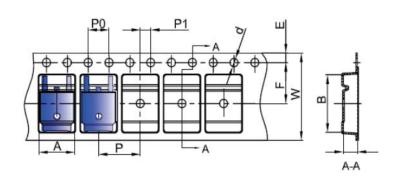
 WW
 = Week

 L
 = Lot Number

Cautions: Molding resin

Epoxy resin UL:94V-0

## **Carrier Tape & Reel Specification DPAK**



SYMBOL	Millimeters		
STWIDOL	Min.	Max.	
Α	6.80	7.00	
В	10.40	10.60	
С	2.60	2.80	
d	Ф1.45	Ф1.65	
E	1.65	1.85	
F	7.40	7.60	
P0	3.90	4.10	
Р	7.90	8.10	
P1	1.90	2.10	
W	15.90	16.30	

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